





100V PNP MEDIUM POWER TRANSISTOR IN SOT89

Features

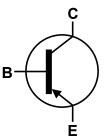
- BV_{CEO} > -100V
- I_C = -1A high Continuous Collector Current
- I_{CM} = -2A Peak Collector Current
- Low saturation voltage V_{CE(sat)} < -200mV @ -250mA
- Complementary NPN type: FCX493
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

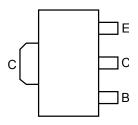
- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208³
- Weight: 0.05 grams (Approximate)







Device Symbol



Top View Pin Out

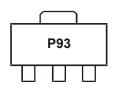
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX593TA	P93	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P93 = Product Type Marking Code



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Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1		
Power Dissipation	(Note 6)	P_{D}	1.5	W	
	(Note 7)		2.0		
	(Note 5)		125	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	83		
	(Note 7)		60		
Thermal Resistance, Junction to Lead (Note 8)		R _{0JL}	22		
Thermal Resistance, Junction to Case	(Note 9)	R _θ JC	16		
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

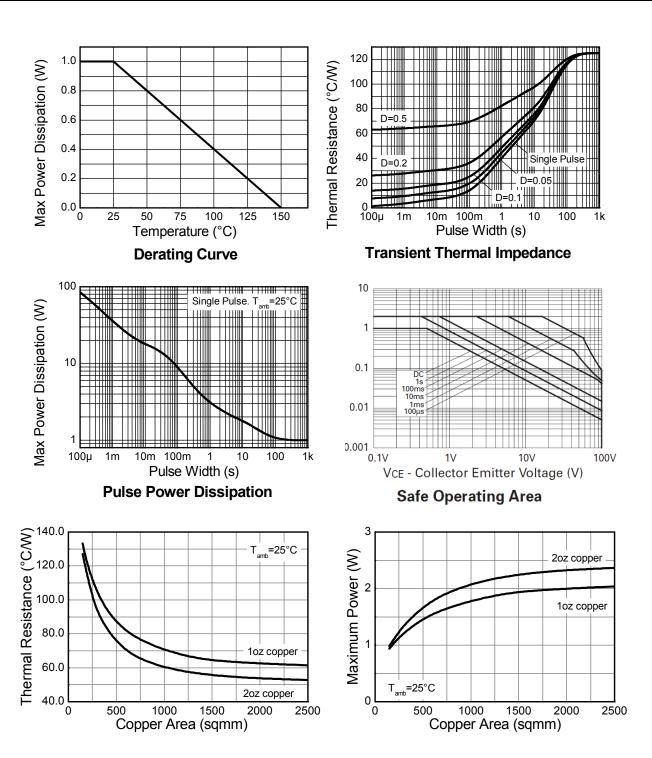
Notes:

- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper. 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 9. Thermal resistance from junction to the top of the case.
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





Thermal Characteristics and Derating Information







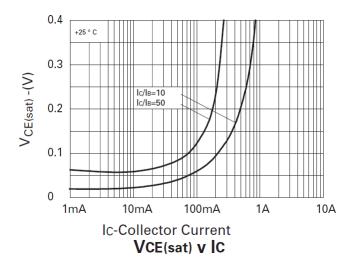
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

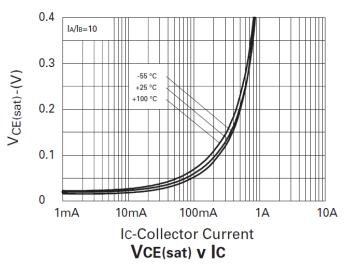
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-120	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -100V
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -5V
Emitter Cutoff Current	I _{CES}	_	_	-100	nA	V _{CES} = -100V
DC current transfer Static ratio (Note 11)	h _{FE}	100 100 100 50	_	— 300 —	_	$\begin{split} & I_{C} = -1 \text{mA}, \ V_{CE} = -5 \text{V} \\ & I_{C} = -250 \text{mA}, \ V_{CE} = -5 \text{V} \\ & I_{C} = -500 \text{mA}, \ V_{CE} = -5 \text{V} \\ & I_{C} = -1 \text{A}, \ V_{CE} = -5 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}		_	-0.2 -0.3	V	I_C = -250mA, I_B = -25mA I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	-1.1	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(on)}	_	_	-1.0	V	$I_C = -1 \text{mA}, V_{CE} = -5 \text{V}$
Transitional Frequency	f _T	50	_	_	MHz	$I_E = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz
Output capacitance	C _{obo}	_	_	5	pF	V _{CB} = -10V, f = 1MHz,

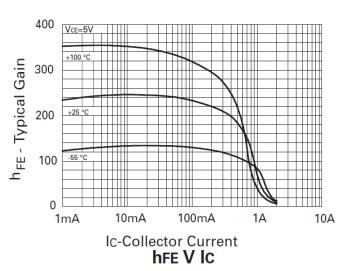
Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

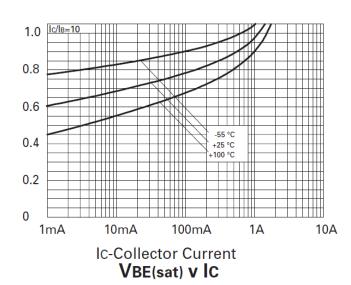


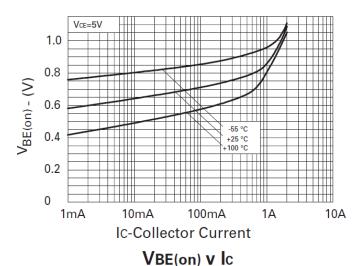
Typical Electrical Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)









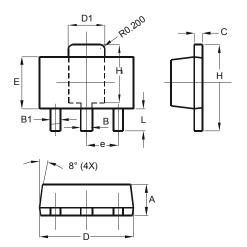






Package Outline Dimensions

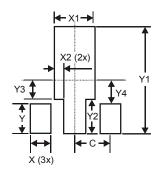
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
Ĺ	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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